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(54) **DIAMOND SEMICONDUCTOR SYSTEM AND METHOD**

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(71) Applicant: **AKHAN Semiconductor, Inc.**, Gurnee, IL (US)

(72) Inventor: **Adam Khan**, Tiburon, CA (US)

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(57)

ABSTRACT

Disclosed herein is a new and improved system and method for fabricating diamond semiconductors. The method may include the steps of selecting a diamond semiconductor material having a surface, exposing the surface to a source gas in an etching chamber, forming a carbide interface contact layer on the surface; and forming a metal layer on the interface layer.

